



1N55-HC2

Power MOSFET

1A, 550V N-CHANNEL POWER MOSFET

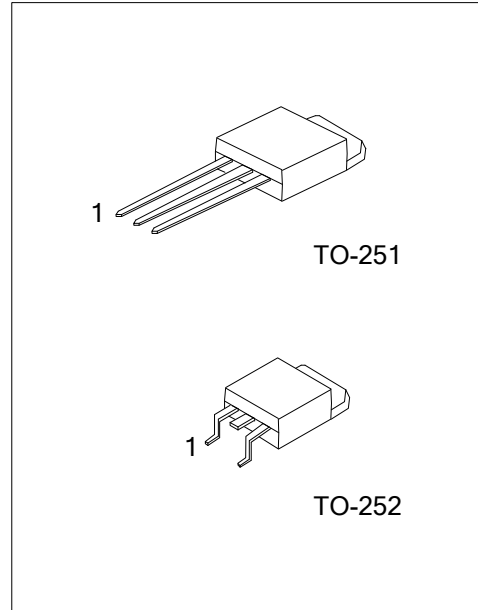
DESCRIPTION

The UTC **1N55-HC2** is an N-channel power MOSFET using UTC's advanced technology to provide customers with a minimum on-state resistance and superior switching performance.

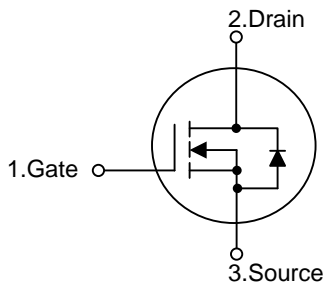
The UTC **1N55-HC2** is generally applied in low power switching mode power appliances and electronic ballast.

FEATURES

- * $R_{DS(ON)} \leq 6.8\Omega$ @ $V_{GS}=10V, I_D=0.5A$
- * High Switching Speed
- * 100% Avalanche Tested



SYMBOL



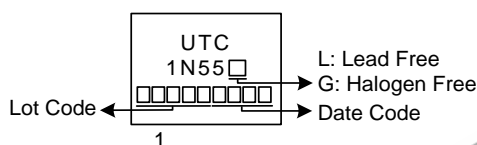
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
1N55L-TM3-T	1N55G-TM3-T	TO-251	G	D	S	Tube
1N55L-TN3-R	1N55G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>1N55G-TM3-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p>	<p>(1) T: Tube, R: Tape Reel</p> <p>(2) TM3: TO-251, TN3: TO-252</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_c=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V _{DSS}	550	V
Gate-Source Voltage		V _{GSS}	±30	V
Drain Current	Continuous	I _D	1	A
	Pulsed (Note 2)	I _{DM}	2	A
Avalanche Energy	Single Pulsed (Note 3)	E _{AS}	24	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.2	V/ns
Power Dissipation		P _D	27	W
Junction Temperature		T _J	+150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. L = 10mH, I_{AS} = 2.2A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C

4. I_{SD} ≤ 1.0A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient		θ _{JA}	100	°C/W
Junction to Case	TO-251/TO-252	θ _{JC}	4.63 (Note)	°C/W

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

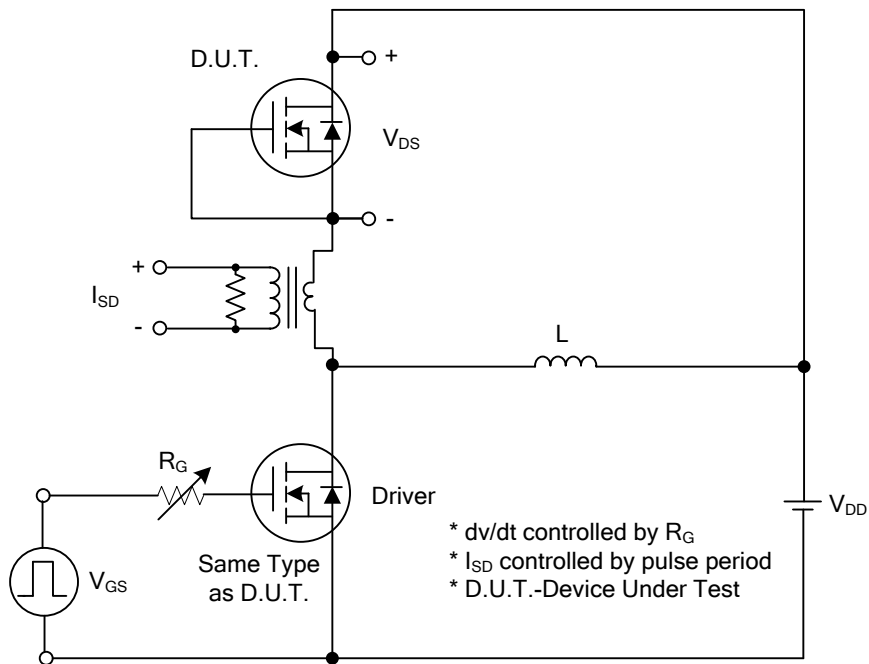
■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =250μA, V _{GS} =0V	550			V	
Drain-Source Leakage Current		I _{DSS}	V _{DS} =550V, V _{GS} =0V			10	μA	
Gate- Source Leakage Current	Forward	I _{GSS}	V _{GS} =+30V, V _{DS} =0V			+100	nA	
	Reverse		V _{GS} =-30V, V _{DS} =0V			-100	nA	
ON CHARACTERISTICS								
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V	
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =0.5A			6.8	Ω	
DYNAMIC PARAMETERS								
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		124.7		pF	
Output Capacitance		C _{OSS}				21		pF
Reverse Transfer Capacitance		C _{RSS}				2.7		pF
SWITCHING PARAMETERS								
Total Gate Charge (Note 1)		Q _G	V _{DS} =440V, V _{GS} =10V, I _D =1A I _G =1mA (Note 1, 2)		5.3		nC	
Gate to Source Charge		Q _{GS}				2.6		nC
Gate to Drain Charge		Q _{GD}				1.1		nC
Turn-ON Delay Time (Note 1)		t _{D(ON)}	V _{DD} =100V, V _{GS} =10V, I _D =1A, R _G =25Ω (Note 1, 2)		8		ns	
Rise Time		t _R				21		ns
Turn-OFF Delay Time		t _{D(OFF)}				166		ns
Fall-Time		t _F				47		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS								
Maximum Body-Diode Continuous Current		I _S				1	A	
Maximum Body-Diode Pulsed Current (Note 1)		I _{SM}				2	A	
Drain-Source Diode Forward Voltage (Note 1)		V _{SD}	I _S =1A, V _{GS} =0V			1.4	V	
Body Diode Reverse Recovery Time		t _{rr}	I _S =1A, V _{GS} =0V,			350	ns	
Body Diode Reverse Recovery Charge		Q _{rr}	di/dt=100A/μs			2.9	μC	

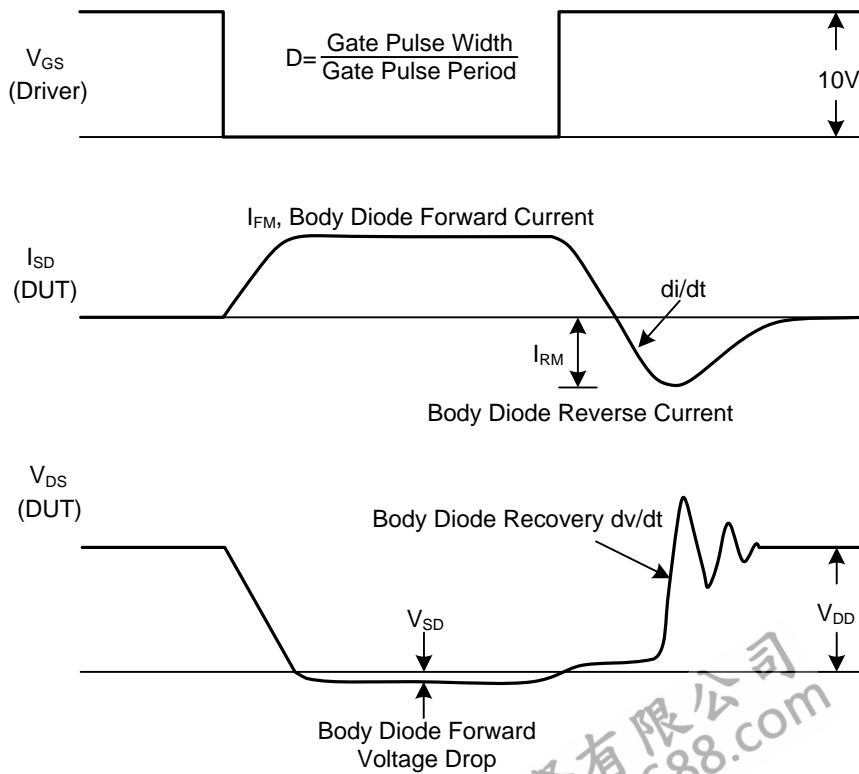
Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.

2. Essentially independent of operating temperature.

TEST CIRCUITS AND WAVEFORMS

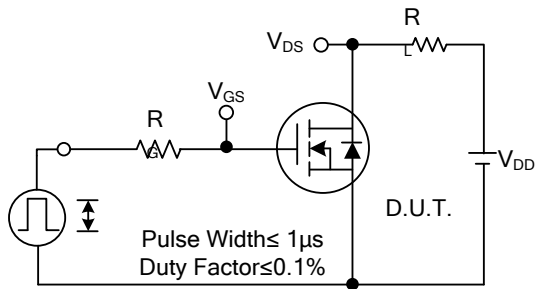


Peak Diode Recovery dv/dt Test Circuit

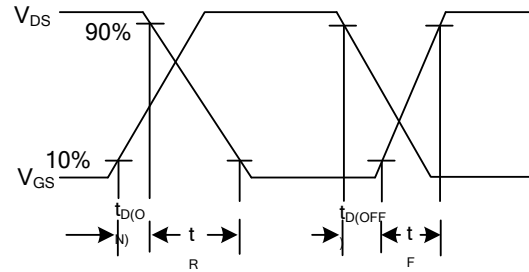


Peak Diode Recovery dv/dt Waveforms

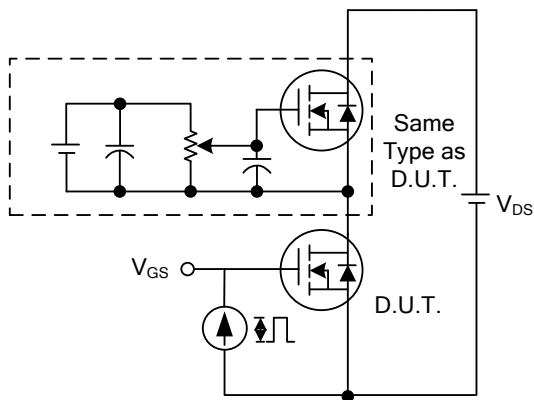
TEST CIRCUITS AND WAVEFORMS



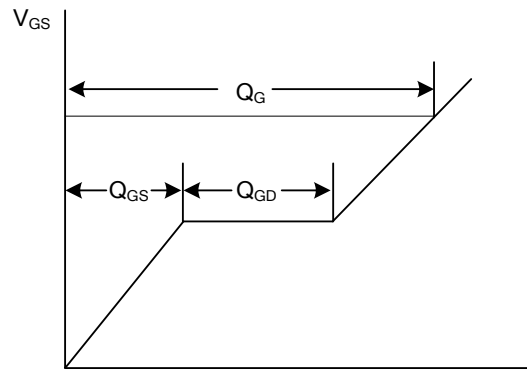
Switching Test Circuit



Switching Waveforms

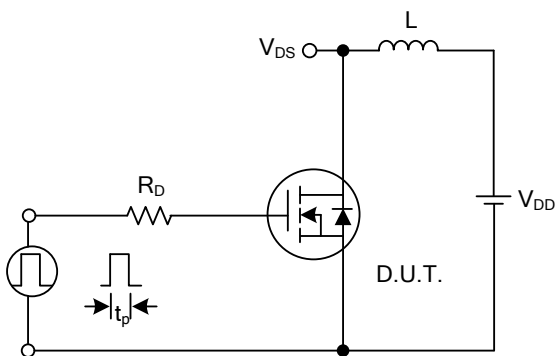


Gate Charge Test Circuit

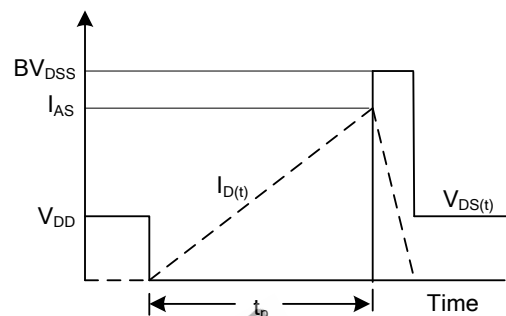


Charge

Gate Charge Waveform

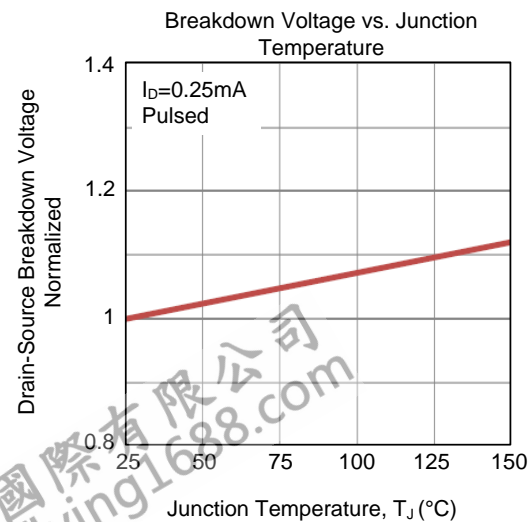
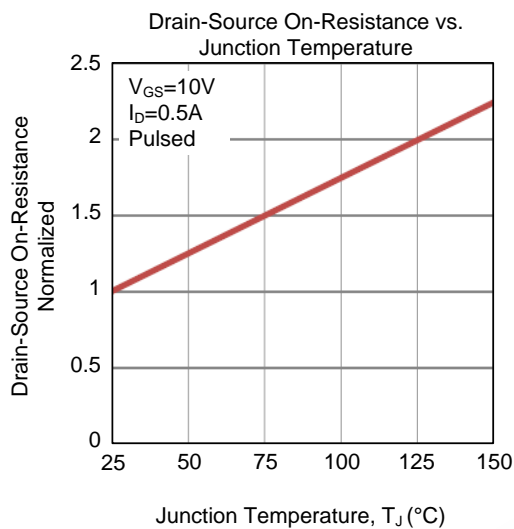
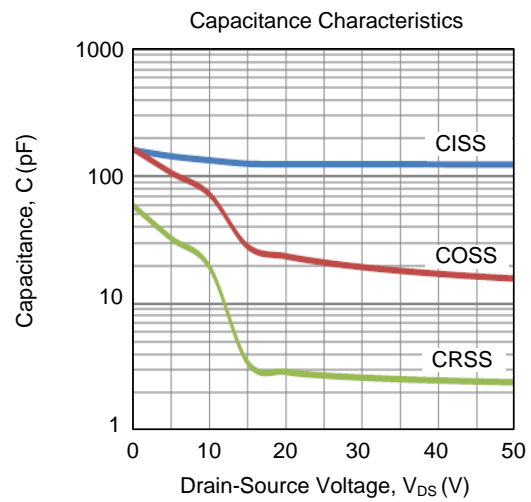
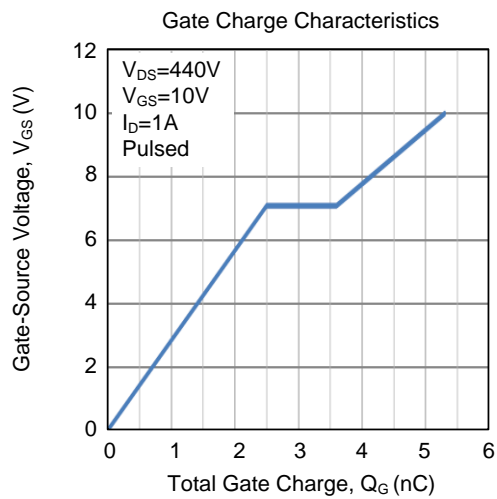
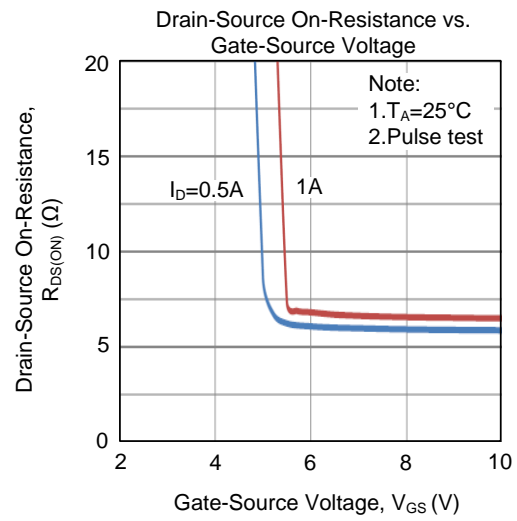
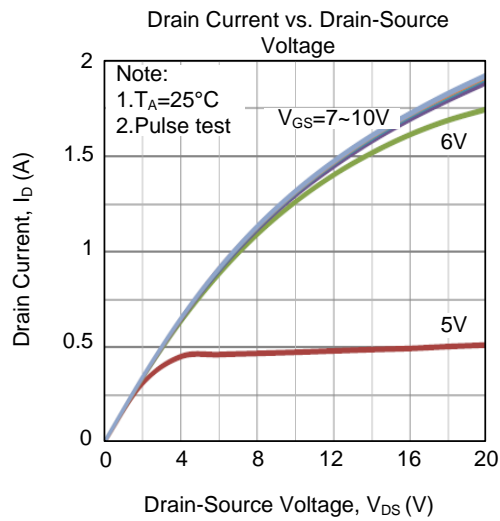


Unclamped Inductive Switching Test Circuit

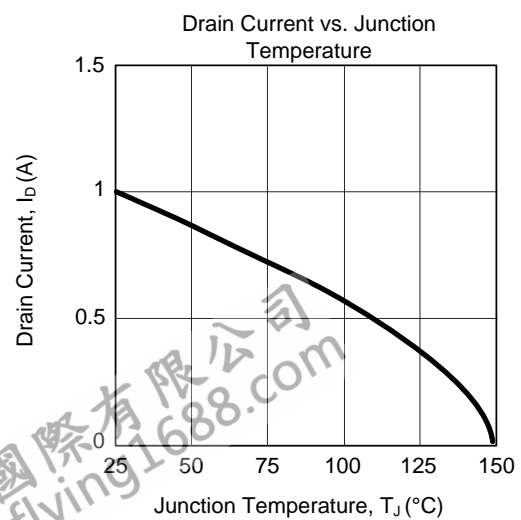
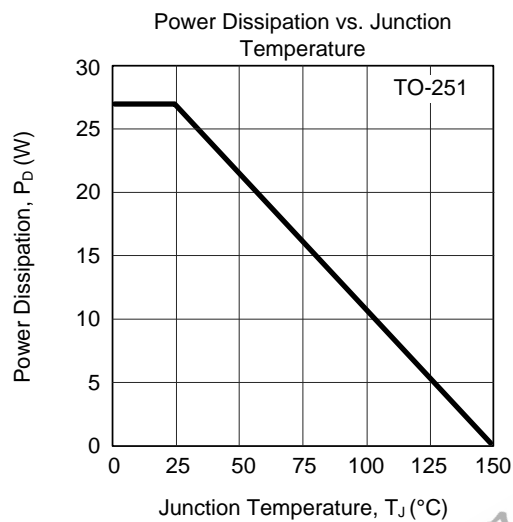
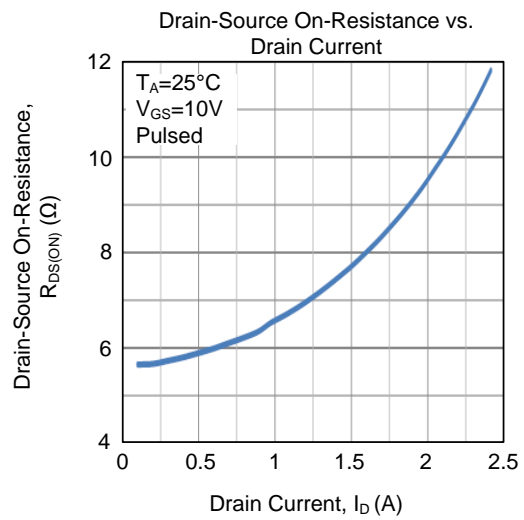
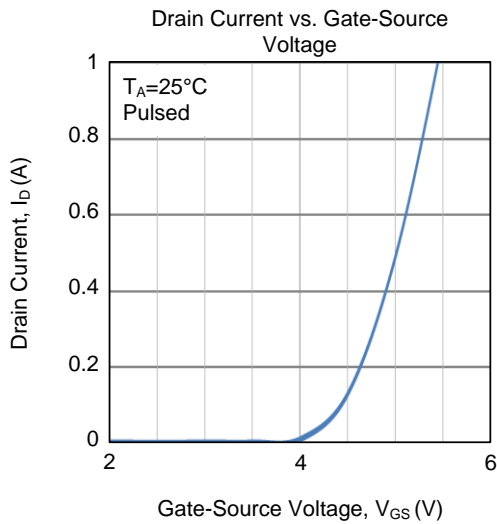
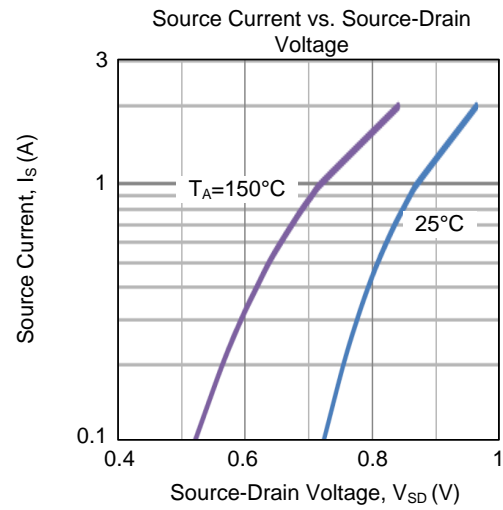
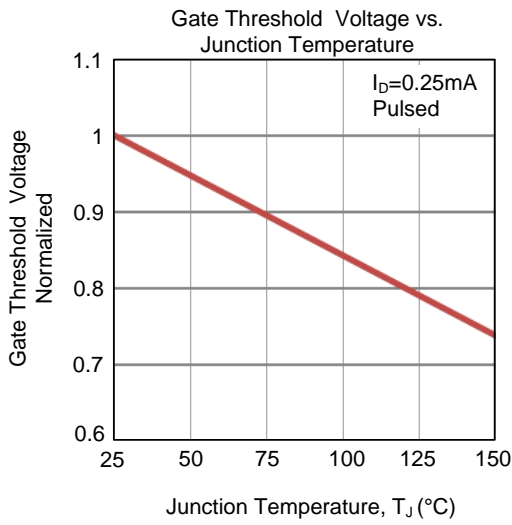


Unclamped Inductive Switching Waveforms

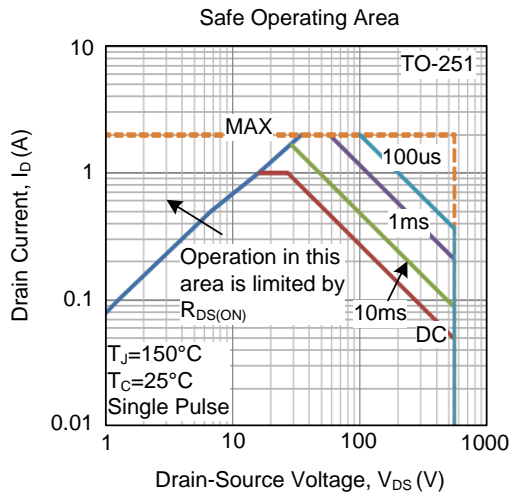
TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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